What is claimed is:

1. A processing method comprising:

forming a metal film on a substrate surface, the substrate surface having at least one feature thereon, the at least one feature having a width defined by a first sidewall and a second sidewall, wherein the metal film is formed on the substrate surface, the first sidewall, the second sidewall, and the bottom surface of the at least one feature, the metal film having a void located within the width of the feature, the void having a first width;

treating the metal film with a plasma to decrease the first width of the void to a second width; and

annealing the metal film to close the void.

2. The method of claim 1, wherein the metal film comprises a metal selected from one or more of tantalum (Ta), titanium (Ti), tungsten (W), molybdenum (Mo), niobium (Nb), vanadium (V), chromium (Cr), cobalt (Co), aluminum (Al), copper (Cu), rubidium (Rb), and the like.

3. The method of claim 1, wherein the plasma comprises nitrogen.

4. The method of claim 1, wherein the plasma is a remote plasma.

5. The method of claim 1, wherein the plasma is a direct plasma.

6. The method of claim 1, wherein the metal film comprises one or more of titanium nitride (TiN), tantalum nitride (TaN), tungsten nitride (WN), molybdenum nitride (MoN), titanium aluminum nitride (TiAlN), niobium nitride (NbN), vanadium nitride (VN), chromium nitride (CrN), rubidium nitride (RbN), and the like.

7. The method of claim 6, wherein the metal film comprises titanium nitride (TiN).

8. The method of claim 1, wherein forming the metal film comprises an atomic layer deposition process.

9. The method of claim 1, wherein the feature has an aspect ratio greater than or equal to 10:1.

10. The method of claim 1, wherein the depth of the at least one feature is in a range of 50 nm to 100 nm.

11. The method of claim 1, wherein the void extends substantially parallel to the first and second sidewalls.

12. A processing method comprising:

forming a film stack on a substrate, the film stack comprising a plurality of alternating layers of an oxide material and a nitride material and the film stack having a stack thickness;

etching the film stack to form an opening extending a depth from a top of the film stack surface to a bottom surface, the opening having a width defined by a first sidewall and a second sidewall;

forming a metal film on the film stack, wherein the metal film is formed on the top of the film stack surface, the first sidewall, the second sidewall, and the bottom surface of the opening, the metal film having a void located within the width of the opening, the void having a first width;

treating the metal film with a plasma to decrease the first width of the void to a second width; and

annealing the metal film to close the void.

13. The method of claim 12, wherein the plasma comprises nitrogen.

14. The method of claim 12, wherein the plasma is a remote plasma.

15. The method of claim 12, wherein the plasma is a direct plasma.

16. The method of claim 12, wherein the metal film comprises one or more of titanium nitride (TiN), tantalum nitride (TaN), tungsten nitride (WN), molybdenum nitride (MoN), titanium aluminum nitride (TiAlN), niobium nitride (NbN), vanadium nitride (VN), chromium nitride (CrN), rubidium nitride (RbN), and the like.

17. The method of claim 12, wherein the void extends substantially parallel to the first and second sidewalls.

18. A non-transitory computer readable medium including instructions, that, when executed by a controller of a processing chamber, causes the processing chamber to perform operations of:

forming a metal film on a substrate surface, the substrate surface having at least one feature thereon, the at least one feature having a width defined by a first sidewall and a second sidewall, wherein the metal film is formed on the substrate surface, the first sidewall, the second sidewall, and the bottom surface of the at least one feature, the metal film having a void located within the width of the feature, the void having a first width;

treating the metal film with a plasma to decrease the first width of the void to a second width; and

annealing the metal film to close the void.

19. The non-transitory computer readable medium of claim 18, wherein the plasma comprises nitrogen.

20. The non-transitory computer readable medium of claim 18, wherein the void extends substantially parallel to the first and second sidewalls.